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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q81061

HAYASHIDA, Hideki, et al.

Appln. No.: 10/821,944

Group Art Unit: 1765

Confirmation No.: 2372

Examiner: Not yet assigned.

Filed: April 12, 2004

For: AMMONIA FOR USE IN MANUFACTURE OF GAN-TYPE COMPOUND
SEMICONDUCTOR AND METHOD FOR MANUFACTURING GAN-TYPE
COMPOUND SEMICONDUCTOR

REQUEST FOR CORRECTED OFFICIAL FILING RECEIPT

ATTN: Office of Initial Patent Examination
Filing Receipt Correction
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

We enclose a copy of the Official Filing Receipt for the above-identified application and
request the following correction(s):

Attorney Docket No.:

Please delete: ~~Q80161~~

Please insert: Q81061


REQUEST FOR CORRECTED OFFICIAL FILING RECEIPT

U.S. Application No.: 10/821,944

Attorney Docket No.: 81061

Verification for the requested correction(s) is indicated on the original date stamped filing receipt for the application filed April 12, 2004.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "Bruce E. Kramer", written over a horizontal line.

Bruce E. Kramer

Registration No. 33,725

SUGHRUE MION, PLLC

Telephone: (202) 293-7060

Facsimile: (202) 293-7860

WASHINGTON OFFICE

23373

CUSTOMER NUMBER

Date: July 20, 2004



UNITED STATES PATENT AND TRADEMARK OFFICE

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APPL NO.	FILING OR 371 (c) DATE	ART UNIT	FIL FEE REC'D	ATTY. DOCKET NO	DRAWINGS	TOT CLMS	IND CLMS
10/821,944	04/12/2004	1765	770	Q80161 Q81061	2	1	1

SUGHRUE, MION, ZINN, MACPEAK & SEAS, PLLC
 2100 Pennsylvania Avenue, N.W.
 Washington, DC 20037-3213

CONFIRMATION NO. 2372

FILING RECEIPT



OC000000013022534

Date Mailed: 06/22/2004

Receipt is acknowledged of this regular Patent Application. It will be considered in its order and you will be notified as to the results of the examination. Be sure to provide the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please write to the Office of Initial Patent Examination's Filing Receipt Corrections, facsimile number 703-746-9195. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections (if appropriate).

Applicant(s)

Hideki Hayashida, Tokyo, JAPAN; ✓
 Taizo Ito, Kanagawa, JAPAN; ✓
 Yasuyuki Sakaguchi, Saitama, JAPAN; ✓

Assignment For Published Patent Application

SHOWA DENKO K.K.; ✓

Domestic Priority data as claimed by applicant

This application is a CON of 09/473,708 12/29/1999 PAT 6,719,842 ✓
 which claims benefit of 60/114,376 12/30/1998 ✓

Foreign Applications

JAPAN HEI. 10-253027 09/07/1998 ✓

If Required, Foreign Filing License Granted: 06/21/2004

Projected Publication Date: 09/30/2004

Non-Publication Request: No

Early Publication Request: No

Title

Ammonia for use in manufacture of GaN-type compound semiconductor and method for manufacturing GaN-type compound semiconductor ✓

Preliminary Class

438

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Title 35, United States Code, Section 184
Title 37, Code of Federal Regulations, 5.11 & 5.15**

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REQUEST OF EARLY NOTIFICATION OF SERIAL NUMBER
Rule 53(b) Continuation of U.S. Application. No. 09/473,708 filed December 29, 1999

Inventor(s): Hideki HAYASHIDA, et al.

Title: AMMONIA FOR USE IN MANUFACTURE OF GAN-TYPE
COMPOUND SEMICONDUCTOR AND METHOD FOR
MANUFACTURING GAN-TYPE COMPOUND SEMICONDUCTOR

Atty Doc. #: Q81061 Client: SHOWA DENKO K.K.

Filing Date: April 12, 2004 # Pgs. Spec/Abst: 19/1 #Claims: 1

Dwg. Sheets: 2 (Figs. 1-4) Decl Copy (4 pages) Prelim Amdt No

IDS/Prior Art: Yes PTO/SB/08 A & B (modified)

Pr Doc: None Asgmt: In the Parent Fee: \$770.00

Copy of Verified English translation of U.S. 60/114,376

☒ Check Attached ☐ Charge to Deposit # 19-4880 Atty/Sec: BEK/lin

SERIAL NO.:

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